

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant(s) : Dureseti CHIDAMBARRAO Group Art Unit: 2813
Appln. No. : 10/715,400 Examiner: J. M. Mitchell
Filed : November 19, 2003 Confirmation No.: 5307
For : SILICON DEVICE ON Si:C-OI AND SGOI AND METHOD OF
MANUFACTURE

SECOND SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents
U.S. Patent and Trademark Office
Customer Service Window, Mail Stop _____
Randolph Building
401 Dulany Street
Alexandria, VA 22314

Sir:

In accordance with Applicants' duty of disclosure under 37 C.F.R. §1.56, and pursuant to the provisions of 37 C.F.R. §§1.97 and 1.98, and supplemental to the Information Disclosure Statements filed November 19, 2003, and December 14, 2005, Applicants hereby direct the Examiner's attention to the documents listed on the enclosed copy of the PTO-1449 Form.

Copies of the cited foreign patent documents and non-patent literature are being submitted herewith. However, pursuant to the U.S. Patent and Trademark Office's decision to waive the requirement under 37 C.F.R 1.98 (a)(2)(i), copies of the cited U.S. patents and U.S. published patent applications are not enclosed herewith. If any copies are needed, the Examiner is respectfully requested to contact the undersigned.

Accordingly, the Examiner is requested to consider these documents and to indicate such consideration by returning a signed and initialed copy of the PTO-1449 Form with the next official communication.

This citation does not constitute an admission that the references are relevant or material to the claims. They are only cited as constituting related art of which the Applicants are aware.

Applicants note that this Second Supplemental Information Disclosure Statement is being filed after receipt of the first action on the merits from the U.S. Patent and Trademark Office and prior to the mailing date of either a final rejection under 37 C.F.R. 1.113 or a Notice of Allowance under 37 C.F.R. 1.311. Accordingly, Applicants hereby authorize the Commissioner to charge \$180.00, or whatever fees are deemed necessary, to Deposit Account No. 09-0458 to ensure consideration of the documents cited herein.

Should there be any questions concerning this application, the Examiner is invited to contact the undersigned at the below-listed telephone number.

Respectfully submitted,
Dureseti CHIDAMBARRAO



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May 8, 2006
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FORM PTO-1449		U.S. Department of Commerce Patent and Trademark Office		Atty. Docket No. FIS920030242US1	Application No. 10/715,400		
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)		Applicant Dureseti CHIDAMBARRAO					
		Filing Date 11/19/2003		Group 2813			
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
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		JP 64-76755	3-22-1989	Japan			
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)							
EXAMINER		DATE CONSIDERED					
*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							

FORM PTO-1449		U.S. Department of Commerce Patent and Trademark Office		Atty. Docket No. FIS920030242US1	Application No. 10/715,400		
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U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
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		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES NO
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